

Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	40	mA
				50	
I_H	$I_T=100mA$		MAX.	30	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150$		MIN.	1200	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150$		MIN.	8	A/ms
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	3	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=5.5A$ $t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=150$	0.6	V
R_D	Dynamic resistance	$T_j=150$	129	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	0.8	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	4	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION

T	04	35	H	-6	F
Triacs					F:TO-220F(Ins)
IT(RMS):4A					
	35:IGT1-3 0.35mA			6:VDRM /VRRM 1 600V	
			High junction temperature		

MARKING

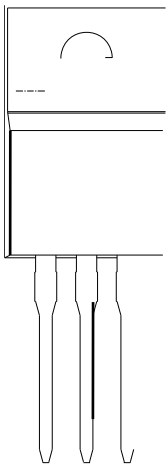


FIG.1: Maximum power dissipation versus RMS on-state current

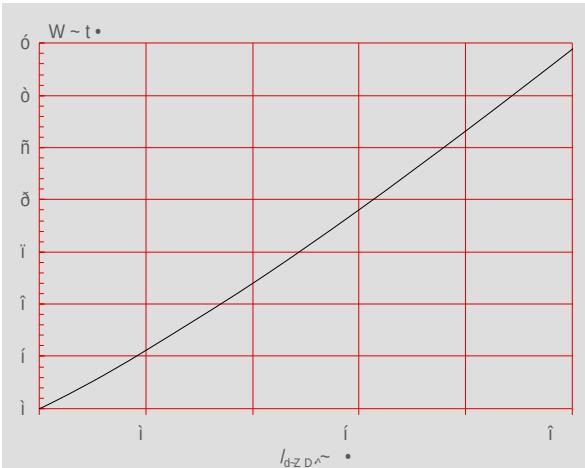


FIG.3: Surge peak on-state current versus number of cycles

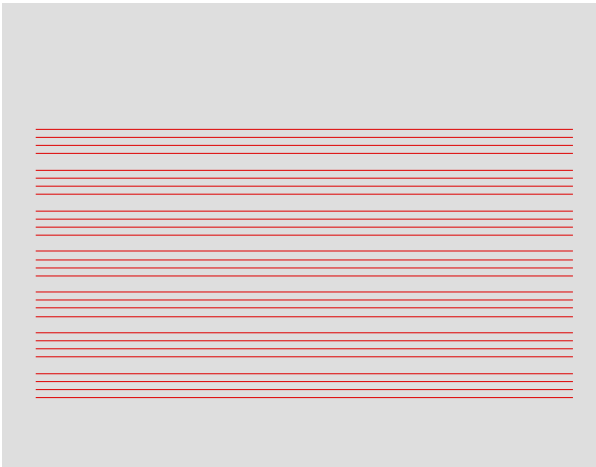


FIG.2: RMS on-state current versus case temperature

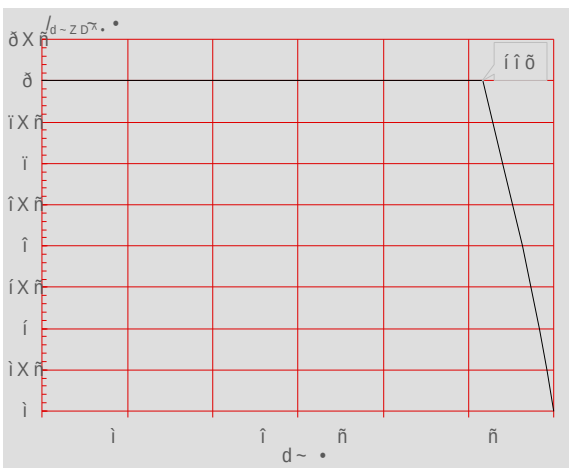


FIG.4: On-state characteristics



ORDERING INFORMATION

Order code	Voltage V _{DRM} /V _{RPM} (V)	IGT(Ma)	Package	Base qty. (pcs)	Delivery mode
		- -			
T0435H-6F	600	35	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated
Oct.10, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA



PACKAGE MECHANICAL DATA



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